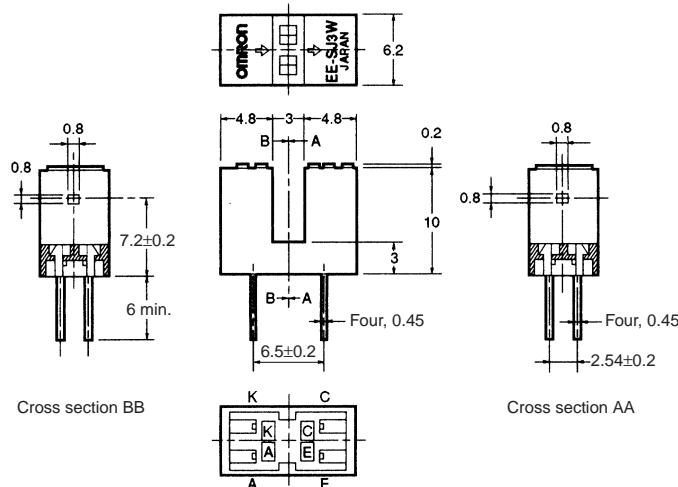


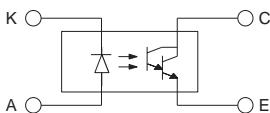
Photomicrosensor (Transmissive) EE-SJ3W-B

■ Dimensions

Note: All units are in millimeters unless otherwise indicated.



Internal Circuit



Terminal No.	Name
A	Anode
K	Cathode
C	Collector
E	Emitter

Unless otherwise specified, the tolerances are as shown below.

Dimensions	Tolerance
3 mm max.	±0.3
3 < mm ≤ 6	±0.375
6 < mm ≤ 10	±0.45
10 < mm ≤ 18	±0.55
18 < mm ≤ 30	±0.65

■ Features

- General-purpose model with a 3-mm-wide slot.
- PCB mounting type.
- With a red LED as an emitter element and a Photo-Darlington transistor as a detector element.

■ Absolute Maximum Ratings ($T_a = 25^\circ\text{C}$)

Item		Symbol	Rated value
Emitter	Forward current	I_F	15 mA (see note 1)
	Pulse forward current	I_{FP}	---
	Reverse voltage	V_R	4 V
Detector	Collector-Emitter voltage	V_{CEO}	24 V
	Emitter-Collector voltage	V_{ECO}	---
	Collector current	I_C	20 mA
	Collector dissipation	P_c	75 mW (see note 1)
	Ambient temperature	T_{opr}	-20°C to 60°C
Ambient temperature	Storage	T_{stg}	-20°C to 80°C
	Soldering temperature	T_{sol}	260°C (see note 3)

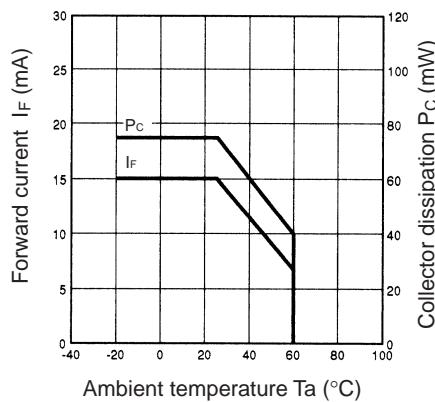
- Note:**
- Refer to the temperature rating chart if the ambient temperature exceeds 25°C.
 - The pulse width is 10 μs maximum with a frequency of 100 Hz.
 - Complete soldering within 10 seconds.

■ Electrical and Optical Characteristics ($T_a = 25^\circ\text{C}$)

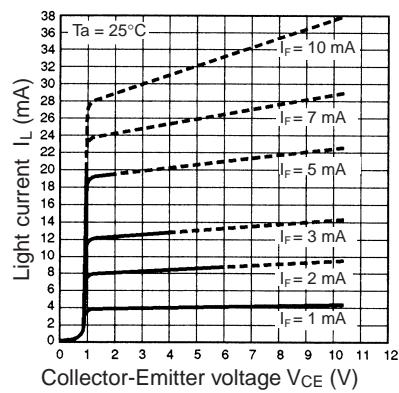
Item		Symbol	Value	Condition
Emitter	Forward voltage	V_F	2.0 V typ., 2.6 V max.	$I_F = 15 \text{ mA}$
	Reverse current	I_R	0.01 μA typ., 5 μA max.	$V_R = 4 \text{ V}$
	Peak emission wavelength	λ_p	700 nm typ.	$I_F = 3 \text{ mA}$
Detector	Light current	I_L	1.5 mA min., 120 mA max.	$I_F = 3 \text{ mA}, V_{CE} = 10 \text{ V}$
	Dark current	I_D	20 nA typ., 250 nA max.	$V_{CE} = 10 \text{ V}, 0 \text{ lx}$
	Leakage current	I_{LEAK}	---	---
	Collector-Emitter saturated voltage	$V_{CE} (\text{sat})$	0.9 V typ.	$I_F = 3 \text{ mA}, I_L = 0.5 \text{ mA}$
	Peak spectral sensitivity wavelength	λ_p	800 nm typ.	$V_{CE} = 10 \text{ V}$
Rising time		tr	180 μs typ.	$V_{CC} = 5 \text{ V}, R_L = 100 \Omega, I_L = 10 \text{ mA}$
Falling time		tf	60 μs typ.	$V_{CC} = 5 \text{ V}, R_L = 100 \Omega, I_L = 10 \text{ mA}$

■ Engineering Data

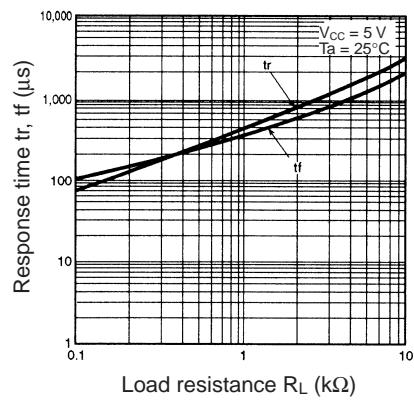
Forward Current vs. Collector Dissipation Temperature Rating



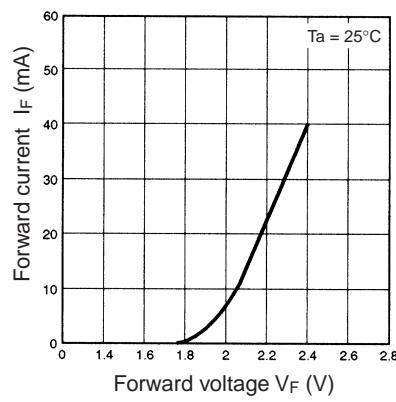
Light Current vs. Collector-Emitter Voltage Characteristics (Typical)



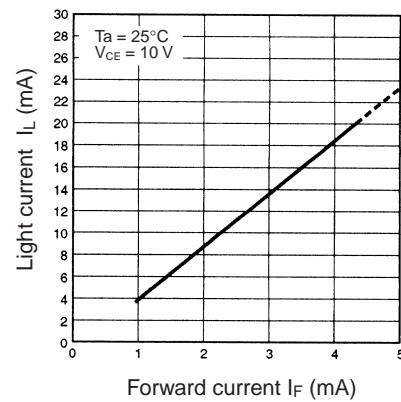
Response Time vs. Load Resistance Characteristics (Typical)



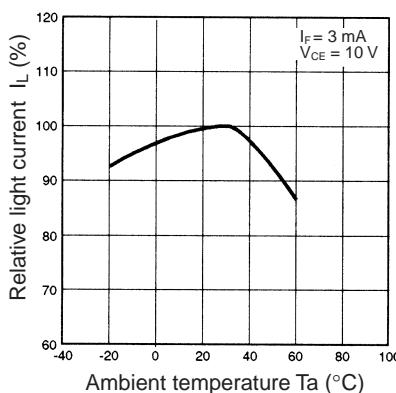
Forward Current vs. Forward Voltage Characteristics (Typical)



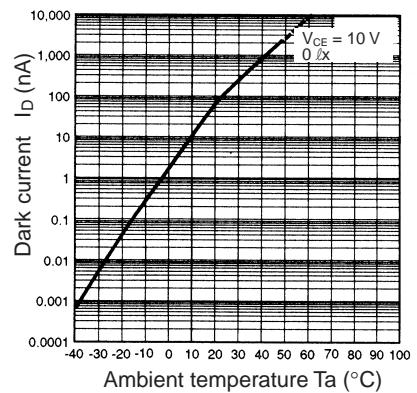
Light Current vs. Forward Current Characteristics (Typical)



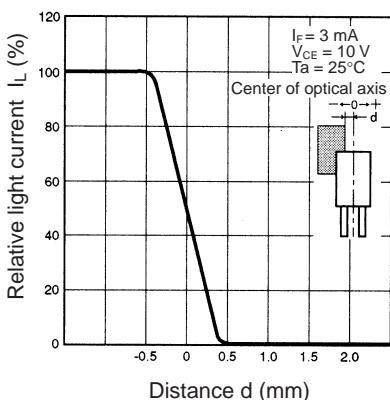
Relative Light Current vs. Ambient Temperature Characteristics (Typical)



Dark Current vs. Ambient Temperature Characteristics (Typical)



Sensing Position Characteristics (Typical)



Response Time Measurement Circuit

